

RJP63K2DPP-M0

Silicon N Channel IGBT
High Speed Power Switching

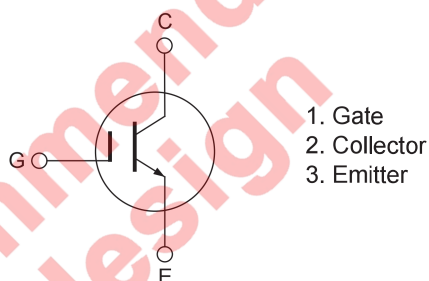
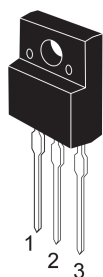
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Features

- Trench gate and thin wafer technology (G6H-II series)
- Low collector to emitter saturation voltage: $V_{CE(sat)} = 1.9\text{ V typ}$
- High speed switching: $t_r = 60\text{ ns typ}$, $t_f = 200\text{ ns typ}$.
- Low leak current: $I_{CES} = 1\text{ }\mu\text{A max}$
- Isolated package TO-220FL

Outline

RENESAS Package code: PRSS0003AF-A)
(Package name: TO-220FL)



Absolute Maximum Ratings

($T_a = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Collector to emitter voltage	V_{CES}	630	V
Gate to emitter voltage	V_{GES}	± 30	V
Collector current	I_C	35	A
Collector peak current	$i_{c(peak)}$ ^{Note1}	200	A
Collector dissipation	P_C ^{Note2}	25	W
Junction to case thermal impedance	θ_{j-c}	5	$^\circ\text{C/W}$
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Notes: 1. $PW \leq 10\text{ }\mu\text{s}$, duty cycle $\leq 1\%$
2. $T_c = 25^\circ\text{C}$